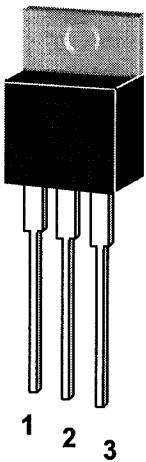


ST H1061

NPN Plastic Power Transistor
Low frequency power amplifier



1. Base 2. Collector 3. Emitter

TO-220 Plastic Package

Absolute Maximum Ratings ($T_a = 25^{\circ}\text{C}$)

	Symbol	Value	Unit
Collector Emitter Voltage	V_{CEO}	50	V
Collector Base Voltage	V_{CBO}	50	V
Emitter Base Voltage	V_{EBO}	4	V
Collector Current	I_{C}	3	A
Power Dissipation	P_{tot}	25	W
Junction Temperature	T_{J}	150	$^{\circ}\text{C}$
Storage Temperature Range	T_{S}	-45 to +150	$^{\circ}\text{C}$

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ST H1061

Characteristics at $T_{amb}=25\text{ }^{\circ}\text{C}$

	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $V_{CE}=4V$, $I_C=1A$	H1061A h_{FE}	35	-	70	-
	H1061B h_{FE}	60	-	120	-
	H1061C h_{FE}	100	-	200	-
at $V_{CE}=4V$, $I_C=0.1A$	H1061D h_{FE}	160	-	320	-
	h_{FE}	35	-	-	-
Collector Cutoff Current at $V_{CB}=20V$	I_{CBO}	-	-	0.1	mA
Collector Saturation Voltage at $I_C=2A$, $I_B=0.2A$	$V_{CE(sat)}$	-	-	1	V
Collector Emitter Breakdown Voltage at $I_C=50mA$	$V_{(BR)CEO}$	50	-	-	V
Collector Base Breakdown Voltage at $I_C=5mA$	$V_{(BR)CBO}$	50	-	-	V
Emitter Base Breakdown Voltage at $I_E=5mA$	$V_{(BR)EBO}$	4	-	-	V
Base Emitter Voltage at $I_C=1A$, $V_{CE}=4V$	V_{BE}	-	-	1.5	V
Gain Bandwidth Product at $V_{CE}=4V$, $I_C=0.5A$	f_T	-	8	-	MHz

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